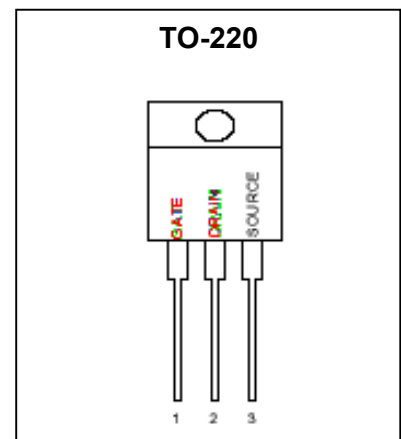
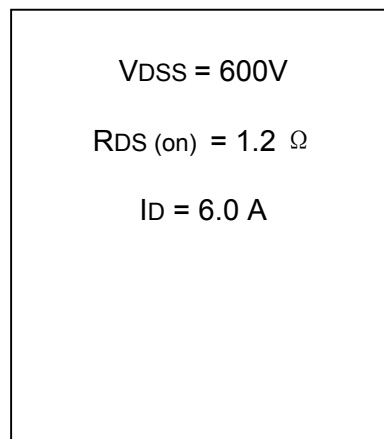
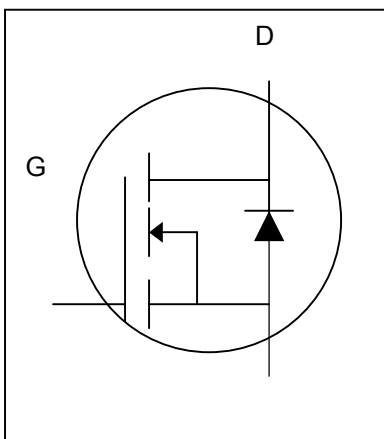


- Advanced Process Technology
- Ultra low On-Resistance Provides Higher Efficiency
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- IDSS and VDS (on) Specified at Elevated Temperature

### DESCRIPTION

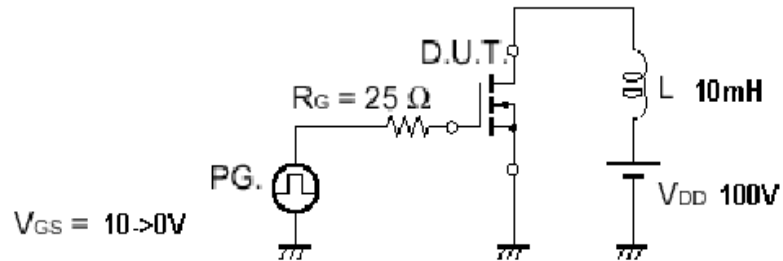
This high voltage MOSFET used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation time. Designed for high voltage, high speed switching application in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operation areas critical and offer additional and safety margin against unexpected voltage transients.



### ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current – Continuous	$I_D$	6.0	A
Gate-to-Source Voltage – Continue - Non-repetitive	$V_{GS}$ $V_{GSM}$	+/- 20 +/- 40	V V
Total Power Dissipation Derate Above 25°C	PD	125 1.0	W W/°C
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy – $T_J = 25^\circ C$ ( $V_{DD} = 100V, V_{GS} = 10V, I_L = 6A, L = 10mH, R_G = 25\Omega$ )	EAS	180	mJ
Thermal Resistance – Junction to Case - Junction to Ambient	$\theta_{JC}$ $\theta_{JA}$	1.0 62.5	°C/W
Maximum Led Temperature for Soldering Purpose, 1/8" from case for 10 seconds	TL	260	°C

## TEST CIRCUIT



Test Circuit – Avalanche Capability

## ELECTRICAL CHARACTERISTICS

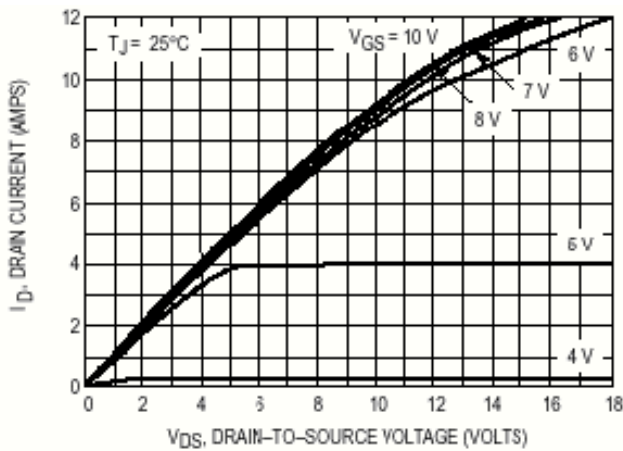
Unless otherwise specified,  $T_J = 25^\circ\text{C}$ .

Characteristic		Symbol	B06N60			Units
			Min	Typ	Max	
Drain-Source Breakdown Voltage ( $V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$ )		$V_{(BR)DSS}$	600			V
Drain-Source Leakage Current ( $V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$ ) ( $V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$ )		$I_{DSS}$			100 50	$\mu\text{A}$
Gate-Source Leakage Current-Forward ( $V_{gsf} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$ )		$I_{GSSF}$			100	nA
Gate-Source Leakage Current-Reverse ( $V_{gsr} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$ )		$I_{GSSR}$			100	nA
Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$ )		$V_{GS(th)}$	2.0		4.0	V
Static Drain-Source On-Resistance ( $V_{GS} = 10\text{ V}$ , $I_D = 3.5\text{A}$ ) *		$R_{DS(on)}$			1.2	$\Omega$
Forward Transconductance ( $V_{DS} = 15\text{ V}$ , $I_D = 3.0\text{A}$ ) *		$g_{FS}$	3.4			mhos
Input Capacitance	$(V_{DS} = 25\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{iss}$		1498	2100	pF
Output Capacitance		$C_{oss}$		158	220	pF
Reverse Transfer Capacitance		$C_{rss}$		29	60	pF
Turn-On Delay Time	$(V_{DD} = 300\text{ V}$ , $I_D = 6.0\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_G = 9.1\Omega$ ) *	$t_{d(on)}$		14	30	ns
Rise Time		$t_r$		19	40	ns
Turn-Off Delay Time		$t_{d(off)}$		40	80	ns
Fall Time		$t_f$		26	55	ns
Total Gate Charge	$(V_{DS} = 300\text{ V}$ , $I_D = 6.0\text{ A}$ , $V_{GS} = 10\text{ V}$ ) *	$Q_g$		35.5	50	nC
Gate-Source Charge		$Q_{gs}$		8.1		nC
Gate-Drain Charge		$Q_{gd}$		14.1		nC
Internal Drain Inductance (Measured from the drain lead 0.25" from package to center of die)		$L_D$		4.5		nH
Internal Drain Inductance (Measured from the source lead 0.25" from package to source bond pad)		$L_S$		7.5		nH
<b>SOURCE-DRAIN DIODE CHARACTERISTICS</b>						
Forward On-Voltage(1)	$(I_S = 6.0\text{ A}$ , $dI_S/dt = 100\text{A}/\mu\text{s}$ )	$V_{SD}$		0.83	1.2	V
Forward Turn-On Time		$t_{on}$		**		ns
Reverse Recovery Time		$t_{rr}$		266		ns

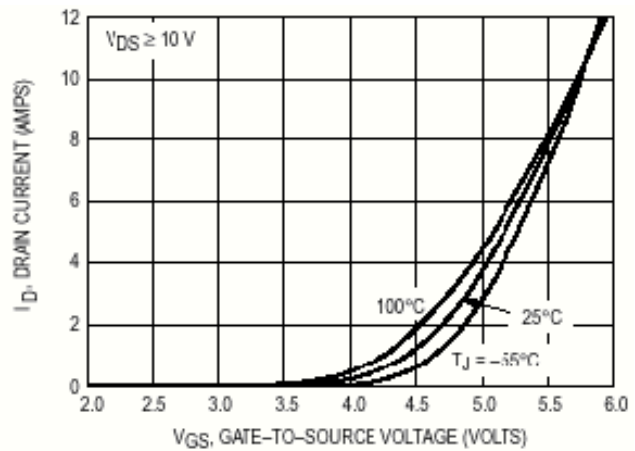
\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

\*\* Negligible, Dominated by circuit inductance

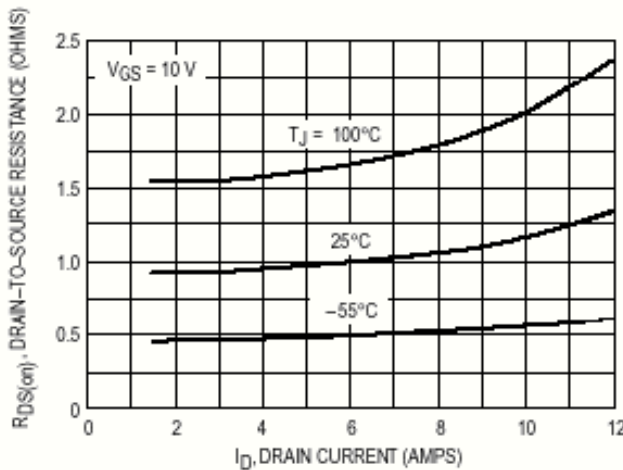
**TYPICAL ELECTRICAL CHARACTERISTICS**



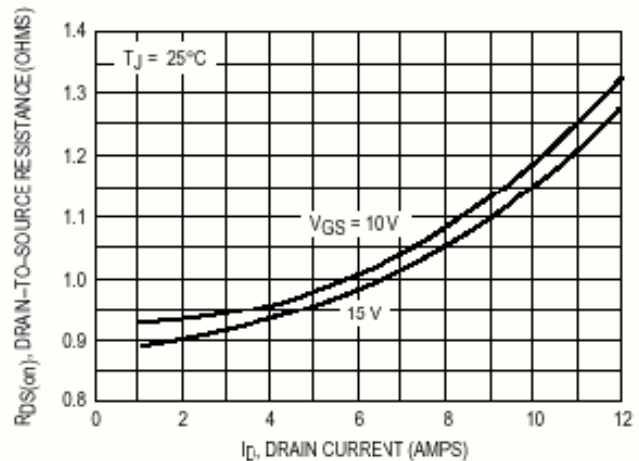
**Figure 1. On-Region Characteristics**



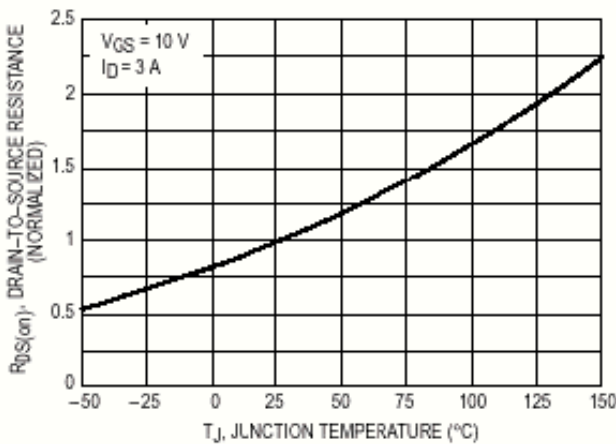
**Figure 2. Transfer Characteristics**



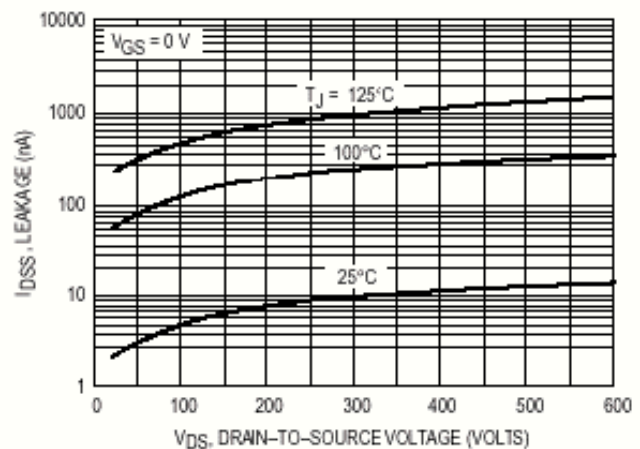
**Figure 3. On-Resistance versus Drain Current and Temperature**



**Figure 4. On-Resistance versus Drain Current and Gate Voltage**



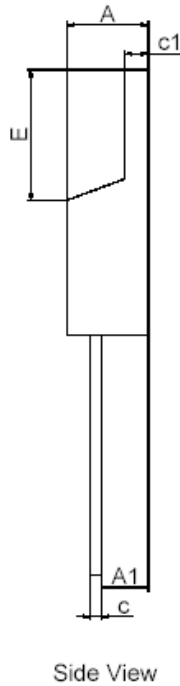
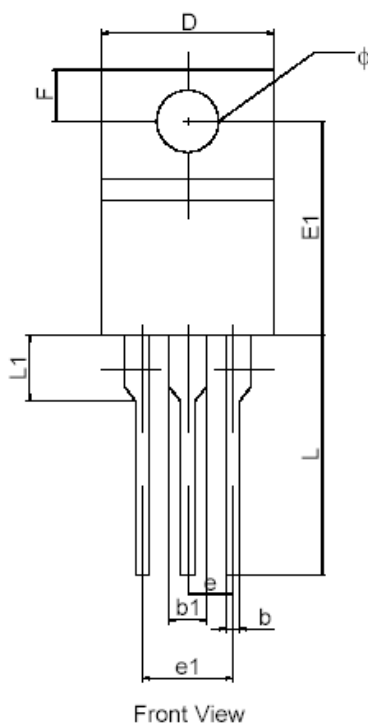
**Figure 5. Cn-Resistance Variation with Temperature**



**Figure 6. Drain-to-Source Leakage Current versus Voltage**

**PACKAGE DIMENSION**

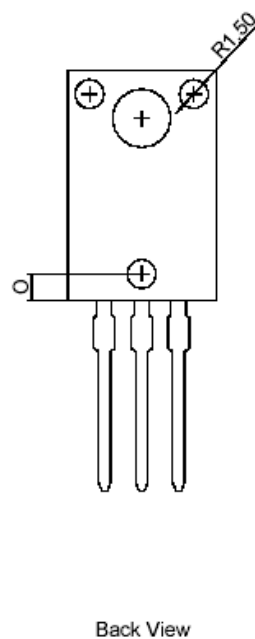
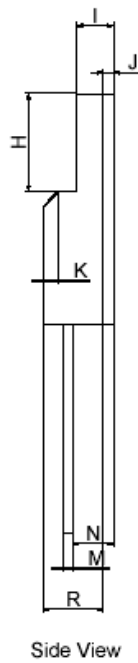
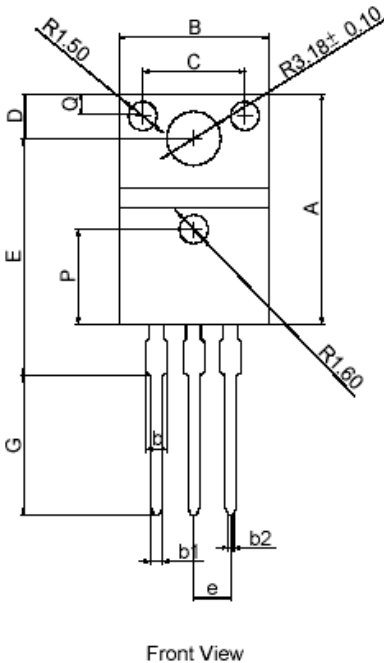
**TO-220**



PIN 1: GATE  
PIN 2: DRAIN  
PIN 3: SOURCE

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.47	---	4.67	0.176	---	0.184
A1	8.02	---	8.02	0.069	---	0.311
b	0.71	---	0.81	0.028	---	0.030
b1	1.17	---	1.37	0.045	---	0.054
c	0.31	---	0.53	0.012	---	0.021
c1	1.17	---	1.37	0.045	---	0.054
D	10.01	---	10.31	0.394	---	0.408
E	8.60	---	8.60	0.338	---	0.350
E1	12.06	---	12.46	0.475	---	0.491
e	---	2.54	---	---	0.100	---
e1	4.50	---	5.18	0.198	---	0.204
F	2.60	---	2.80	0.102	---	0.114
L	13.40	---	13.80	0.668	---	0.543
L1	3.68	---	3.88	0.144	---	0.160
φ	3.79	---	3.89	0.149	---	0.163

**TO-220FP**



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	16.87	---	18.87	0.667	---	0.750
B	9.95	---	10.26	0.392	---	0.408
C	---	7.00	---	---	0.275	---
D	3.80	---	3.40	0.150	---	0.134
E	15.00	---	15.00	0.594	---	0.590
G	9.45	---	10.00	0.372	---	0.394
H	6.45	---	6.51	0.255	---	0.257
I	2.54	---	2.74	0.100	---	0.108
J	---	0.70	---	---	0.028	---
K	---	1.00	---	---	0.039	---
M	0.45	---	0.60	0.018	---	0.024
N	2.60	---	2.60	0.102	---	0.102
O	---	1.80	---	---	0.071	---
P	---	0.50	---	---	0.019	---
Q	---	1.80	---	---	0.069	---
R	4.50	---	4.30	0.177	---	0.169
b	---	1.27	---	---	0.050	---
b1	0.70	---	0.90	0.028	---	0.035
b2	0.25	---	0.45	0.010	---	0.018
e	---	2.54	---	---	0.100	---

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